

High-speed double diode Rev. 3 — 29 June 2010

Product data sheet

Product profile

1.1 General description

Two high-speed switching diodes fabricated in planar technology, and encapsulated in a small SOT143B Surface-Mounted Device (SMD) plastic package. The diodes are not connected.

1.2 Features and benefits

■ High switching speed: $t_{rr} \le 6$ ns

Reverse voltage: V_R ≤ 60 V

Repetitive peak reverse voltage: V_{RRM} ≤ 60 V Repetitive peak forward current: I_{FRM} ≤ 600 mA

AEC-Q101 qualified

Small SMD plastic package

1.3 Applications

High-speed switching in e.g. surface-mounted circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		[1][2]	-	200	mA
I _R	reverse current	$V_{R} = 60 \text{ V}$	-	-	100	nA
V_R	reverse voltage		-	-	60	V
t _{rr}	reverse recovery time		[3] _	-	6	ns

^[1] Single diode loaded.



^[2] Device mounted on an FR4 Printed-Circuit Board (PCB).

^[3] When switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω ; measured at I_R = 40 mA.

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2. Pinning information

Table 2. Pinning

Table 2.	rinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)	4 3	4 3
3	anode (diode 2)		
4	anode (diode 1)	1 2	
			1 2
			006aab100

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BAS56	-	plastic surface-mounted package; 4 leads	SOT143B	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BAS56	*L5

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse		-	60	V
	voltage		[1] -	120	V
V_R	reverse voltage		-	60	V
			[1] -	120	V
l _F	forward current		[2][3]	200	mA
			[2][4]	150	mA
I _{FRM}	repetitive peak forward		<u>[3]</u> _	600	mA
	current		[4] -	430	mA
I _{FSM}	non-repetitive peak forward current	square wave	<u>[5]</u>		
		t _p = 1 μs	-	9	Α
		t _p = 100 μs	-	3	Α
		$t_p = 10 \text{ ms}$	-	1.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] -	250	mW
Tj	junction temperature		-	150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Series connection.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	360	K/W

^[1] Device mounted on an FR4 PCB.

^[2] Device mounted on an FR4 PCB.

^[3] Single diode loaded.

^[4] Double diode loaded.

^[5] $T_j = 25$ °C prior to surge.

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7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 200 \text{ mA}$	<u>[1]</u> -	-	1	V
I _R	reverse current	$V_R = 60 \text{ V}$	-	-	100	nA
		$V_R = 60 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
		V _R = 120 V	[2] _	-	100	nA
		$V_R = 120 \text{ V}; T_j = 150 ^{\circ}\text{C}$	[2] _	-	100	μΑ
C_d	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	2.5	pF
t _{rr}	reverse recovery time		[3]	-	6	ns
V_{FR}	forward recovery voltage		<u>[4]</u> _	-	2	V
			[5] _	-	1.5	V

^[1] $T_{amb} = 25$ °C; device has reached the thermal equilibrium when mounted on an FR4 PCB.

^[2] Series connection.

^[3] When switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω ; measured at I_R = 40 mA.

^[4] When switched from $I_F = 400 \text{ mA}$; $t_r = 30 \text{ ns}$.

^[5] When switched from $I_F = 400 \text{ mA}$; $t_r = 100 \text{ ns}$.

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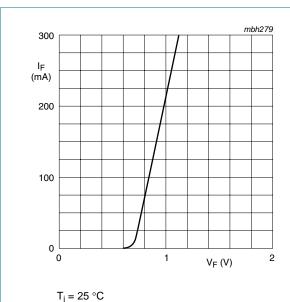
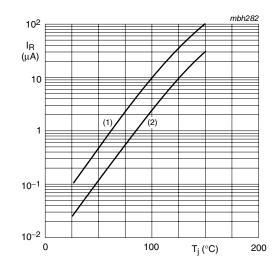


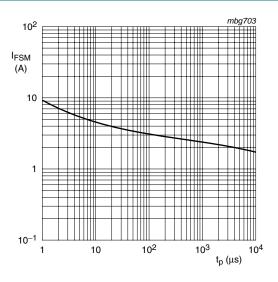
Fig 1. Forward current as a function of forward voltage; typical values



(1) $V_R = 60 \text{ V}$; maximum values

(2) $V_R = 60 \text{ V}$; typical values

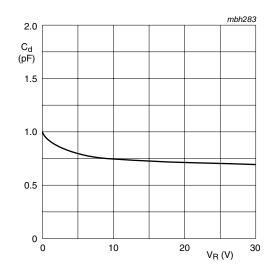
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_i = 25$ °C; prior to surge

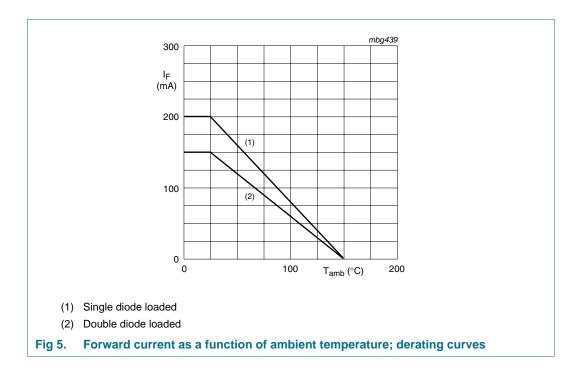
Fig 2. Non-repetitive peak forward current as a function of pulse duration



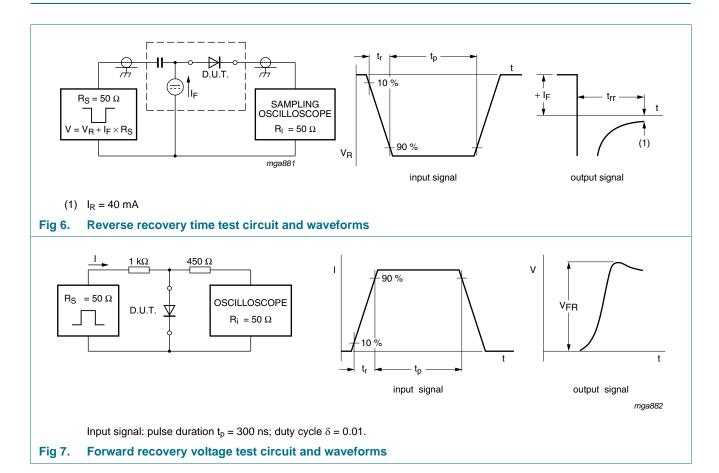
 $f = 1 \text{ MHz}; T_j = 25 \text{ }^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

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8. Test information

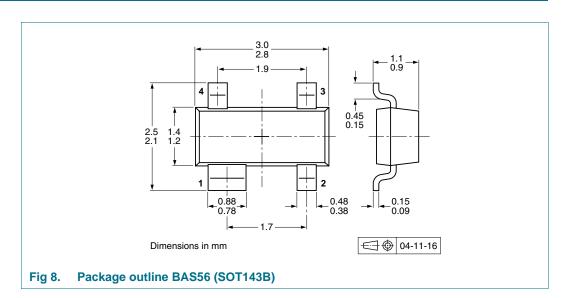


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8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

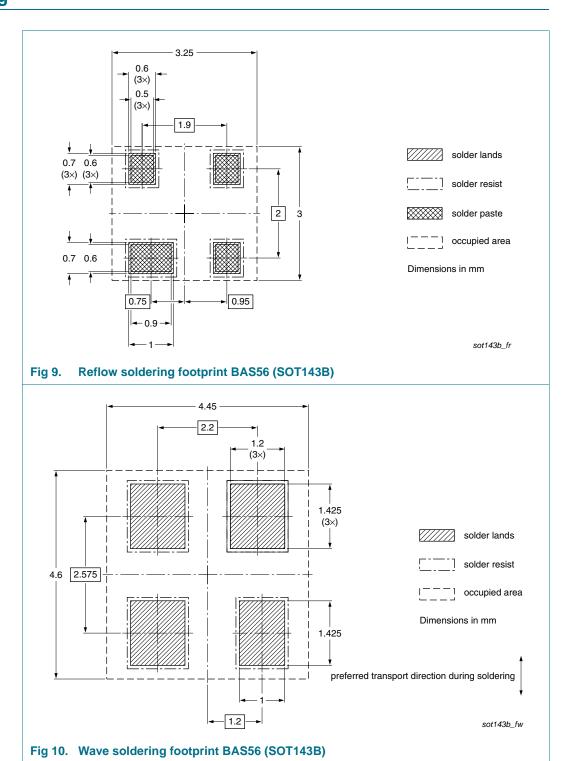
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
BAS56	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235	

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



Product data sheet

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12. Revision history

Table 9. Revision history

Release date	Data sheet status	Change notice	Supersedes			
20100629	Product data sheet	-	BAS56_2			
		redesigned to comply w	rith the new identity			
 Legal texts have been adapted to the new company name where appropriate. 						
• Section 1.1	"General description": amer	nded				
Section 4 "Marking": updated						
Table 1 "Quick reference data": added						
Section 8 "Test information": added						
Figure 8: superseded by minimized package outline drawing						
Section 10 "Packing information": added						
Section 11 "Soldering": added						
 Section 13 ' 	"Legal information": updated	ļ				
19960910	Product specification	-	BAS56_1			
19960423	Product specification	-	-			
	20100629 The format guidelines of Legal texts Section 1.1 Section 4 "N Table 1 "Qu Section 8 "T Figure 8: su Section 10 " Section 11 " Section 13 "	 20100629 Product data sheet The format of this data sheet has been guidelines of NXP Semiconductors. Legal texts have been adapted to the number of the section 1.1 "General description": amendated to section 4 "Marking": updated Table 1 "Quick reference data": added Section 8 "Test information": added Figure 8: superseded by minimized pactors of the section 10 "Packing information": added Section 11 "Soldering": added Section 13 "Legal information": updated 19960910 Product specification 	The format of this data sheet has been redesigned to comply we guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where Section 1.1 "General description": amended Section 4 "Marking": updated Table 1 "Quick reference data": added Section 8 "Test information": added Figure 8: superseded by minimized package outline drawing Section 10 "Packing information": added Section 11 "Soldering": added Section 13 "Legal information": updated			

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BAS56

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BAS56 NXP Semiconductors

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